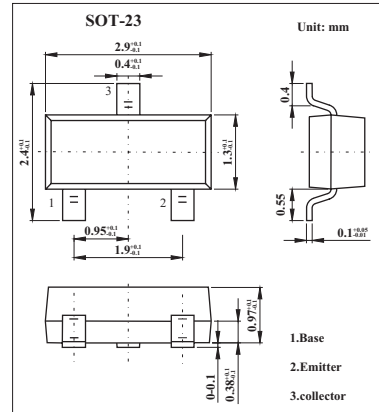


■ Features

- Low current (max. 100 mA).
- Low voltage (max. 32 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	32	V
Collector-emitter voltage	V _{CEO}	32	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _C	100	mA
Peak collector current	I _{CM}	200	mA
Peak base current	I _{BM}	100	mA
Total power dissipation *	P _{tot}	250	mW
Storage temperature	T _{stg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	R _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient *	R _{th j-a}	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	ICBO	IE = 0; VCB = 32 V			100	nA
	ICBO	IE = 0; VCB = 32 V; Tj = 100 °C			10	µA
Emitter cutoff current	IEBO	IC = 0; VEB = 5 V			100	nA
DC current gain	hFE	IC = 10 µA; VCE = 5 V		150		
		IC = 2 mA; VCE = 5 V	200		450	
Collector-emitter saturation voltage	VCE(sat)	IC = 10 mA; IB = 0.5 mA		120	250	mV
		IC = 50 mA; IB = 2.5 mA		210		mV
Base to emitter saturation voltage	VBE(sat)	IC = 10 mA; IB = 0.5 mA		750		mV
		IC = 50 mA; IB = 2.5 mA		850		mV
Base to emitter voltage	VBE	IC = 2 mA; VCE = 5 V	550		700	mV
Collector capacitance	CC	IE = ie = 0; VCB = 10 V; f = 1 MHz		2.5		pF
Transition frequency	fT	IC = 10 mA; VCE = 5 V; f = 100 MHz	100			MHz
Noise figure	NF	IC = 200 µA; VCE = 5 V; RS = 2 kΩ; f = 1 kHz; B = 200 Hz		1.2	4	dB

■ Marking

Marking	D7
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